

ABSTRACT

1 A low temperature process for forming a metal doped
2 silicon layer in which a silicon layer is deposited onto
3 a substrate at low temperatures, with a metal doping
4 layer then deposited upon the silicon layer. This
5 structure is then annealed at low temperatures to form a
6 metal doped semiconductor having greater than about 1 x
7 10^{20} dopant atoms per cm^3 of silicon.